

ZXMD63C03X

30V DUAL N AND P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

N-CHANNEL: $V_{(BR)DSS}=30V$; $R_{DS(ON)}=0.135\Omega$; $I_D=2.3A$

P-CHANNEL: $V_{(BR)DSS}=-30V$; $R_{DS(ON)}=0.185\Omega$; $I_D=-2.0A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



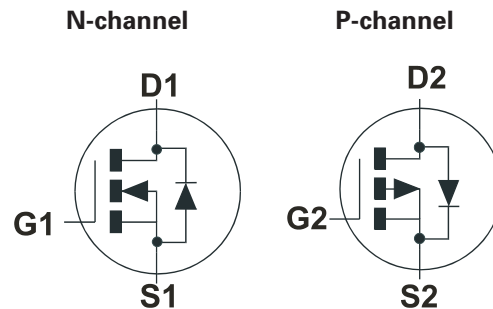
MSOP8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control



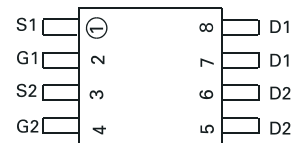
ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXMD63C03XTA	7	12 embossed	1,000
ZXMD63C03XTC	13	12 embossed	4,000

DEVICE MARKING

ZXM63C03

Pin-out



Top view

ZXMD63C03X

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage	V_{DSS}	30	-30	V
Gate- Source Voltage	V_{GS}	± 20		V
Continuous Drain Current ($V_{GS}=4.5V$; $T_A=25^{\circ}C$)(b)(d) ($V_{GS}=4.5V$; $T_A=70^{\circ}C$)(b)(d)	I_D	2.3 1.8	-2.0 -1.6	A A
Pulsed Drain Current (c)(d)	I_{DM}	14	-9.6	A
Continuous Source Current (Body Diode)(b)(d)	I_S	1.5	-1.4	A
Pulsed Source Current (Body Diode)(c)(d)	I_{SM}	14	-9.6	A
Power Dissipation at $T_A=25^{\circ}C$ (a)(d) Linear Derating Factor	P_D	0.87 6.9		W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (a)(e) Linear Derating Factor	P_D	1.04 8.3		W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b)(d) Linear Derating Factor	P_D	1.25 10		W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150		$^{\circ}C$

THERMAL RESISTANCE

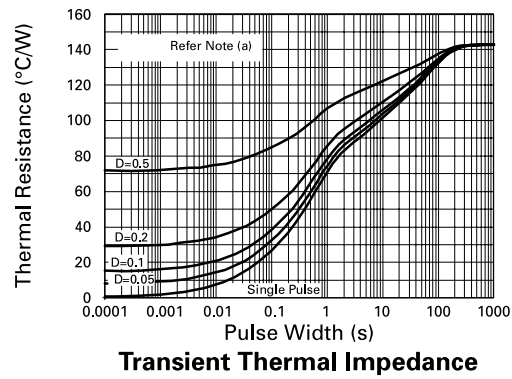
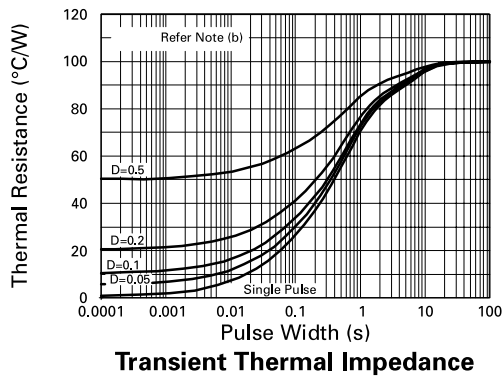
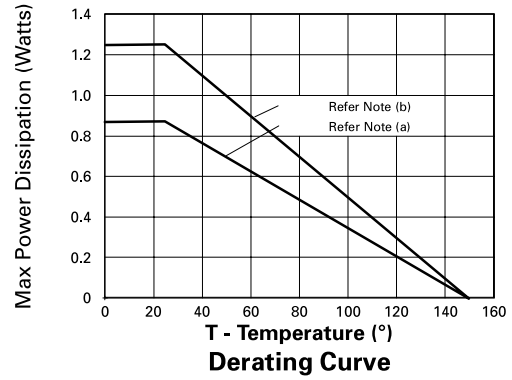
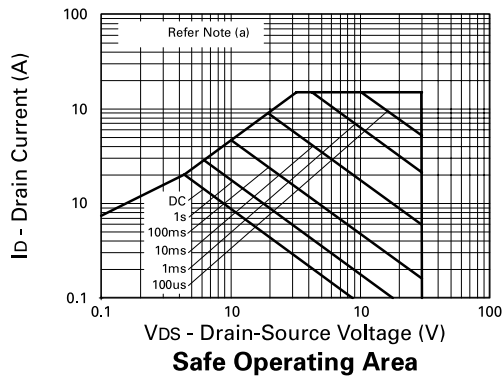
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	143	$^{\circ}C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	100	$^{\circ}C/W$
Junction to Ambient (a)(e)	$R_{\theta JA}$	120	$^{\circ}C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
 (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
 (c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
 (d) For device with one active die.
 (e) For device with two active die running at equal power.

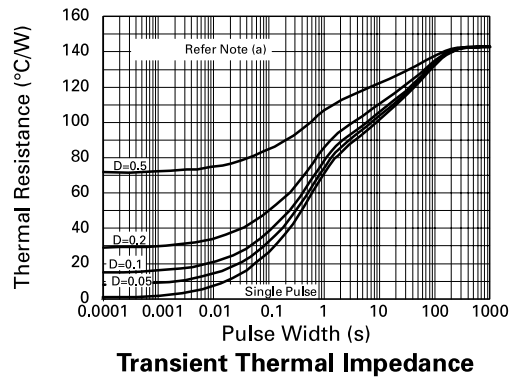
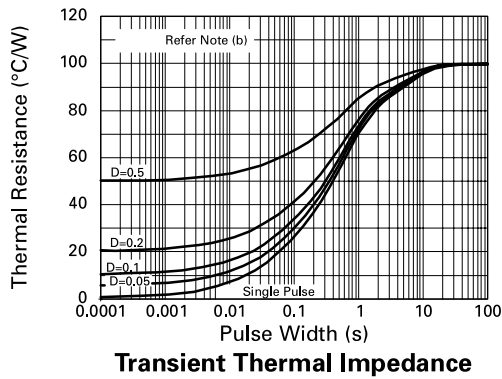
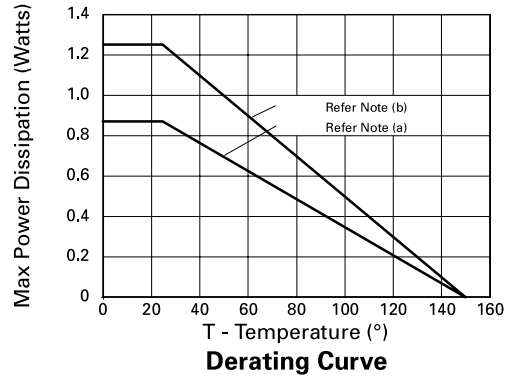
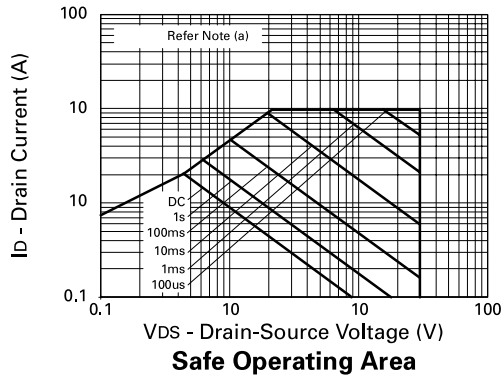
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N-CHANNEL CHARACTERISTICS



ZXMD63C03X

P-CHANNEL CHARACTERISTICS



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N-CHANNEL ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

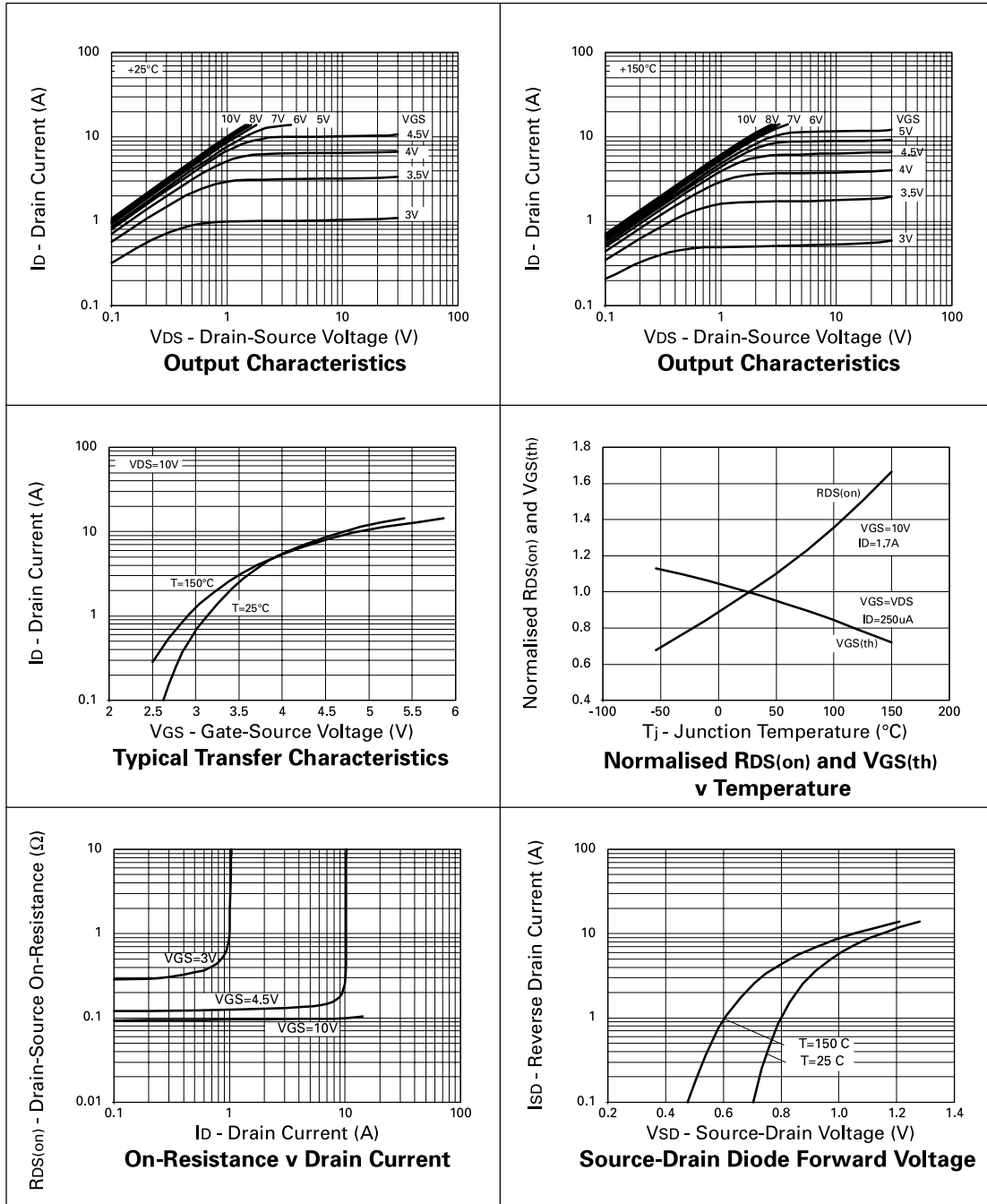
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =± 20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1.0			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.135 0.200	Ω Ω	V _{GS} =10V, I _D =1.7A V _{GS} =4.5V, I _D =0.85A
Forward Transconductance (3)	g _{fs}	1.9			S	V _{DS} =10V,I _D =0.85A
DYNAMIC (3)						
Input Capacitance	C _{iss}		290		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{Oss}		70		pF	
Reverse Transfer Capacitance	C _{rss}		20		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		2.5		ns	V _{DD} =15V, I _D =1.7A R _G =6.1Ω, R _D =8.7Ω (Refer to test circuit)
Rise Time	t _r		4.1		ns	
Turn-Off Delay Time	t _{d(off)}		9.6		ns	
Fall Time	t _f		4.4		ns	
Total Gate Charge	Q _g			8	nC	V _{DS} =24V,V _{GS} =10V, I _D =1.7A (Refer to test circuit)
Gate-Source Charge	Q _{gs}			1.2	nC	
Gate Drain Charge	Q _{gd}			2	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _j =25°C, I _S =1.7A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		16.9		ns	T _j =25°C, I _F =1.7A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q _{rr}		9.5		nC	

NOTES:

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

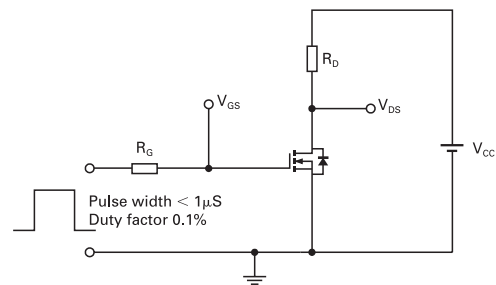
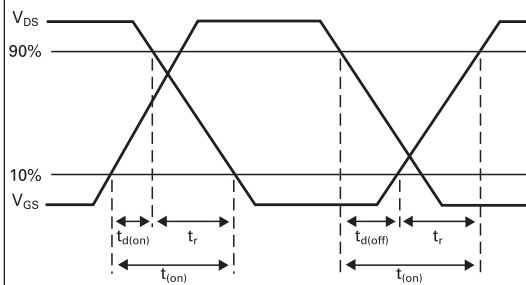
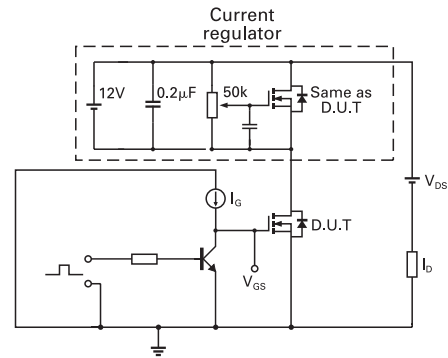
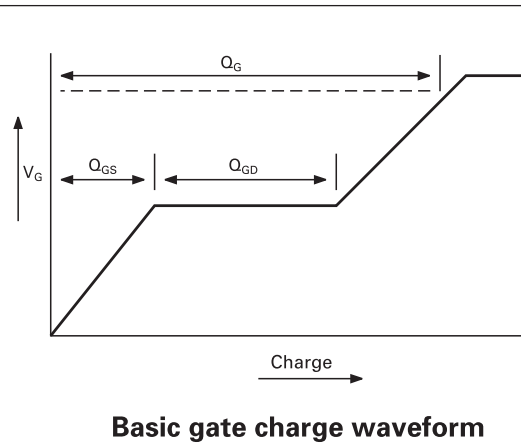
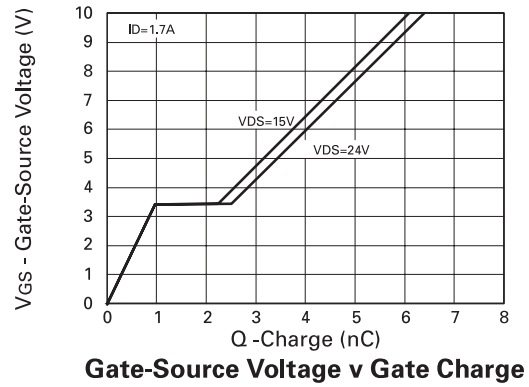
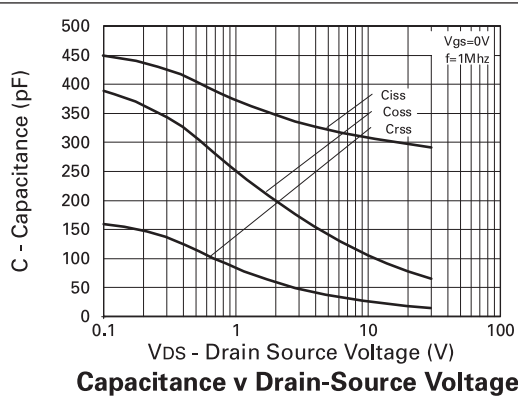
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N-CHANNEL TYPICAL CHARACTERISTICS



ZXMD63C03X

N-CHANNEL CHARACTERISTICS



ZXMD63C03X

P-CHANNEL

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

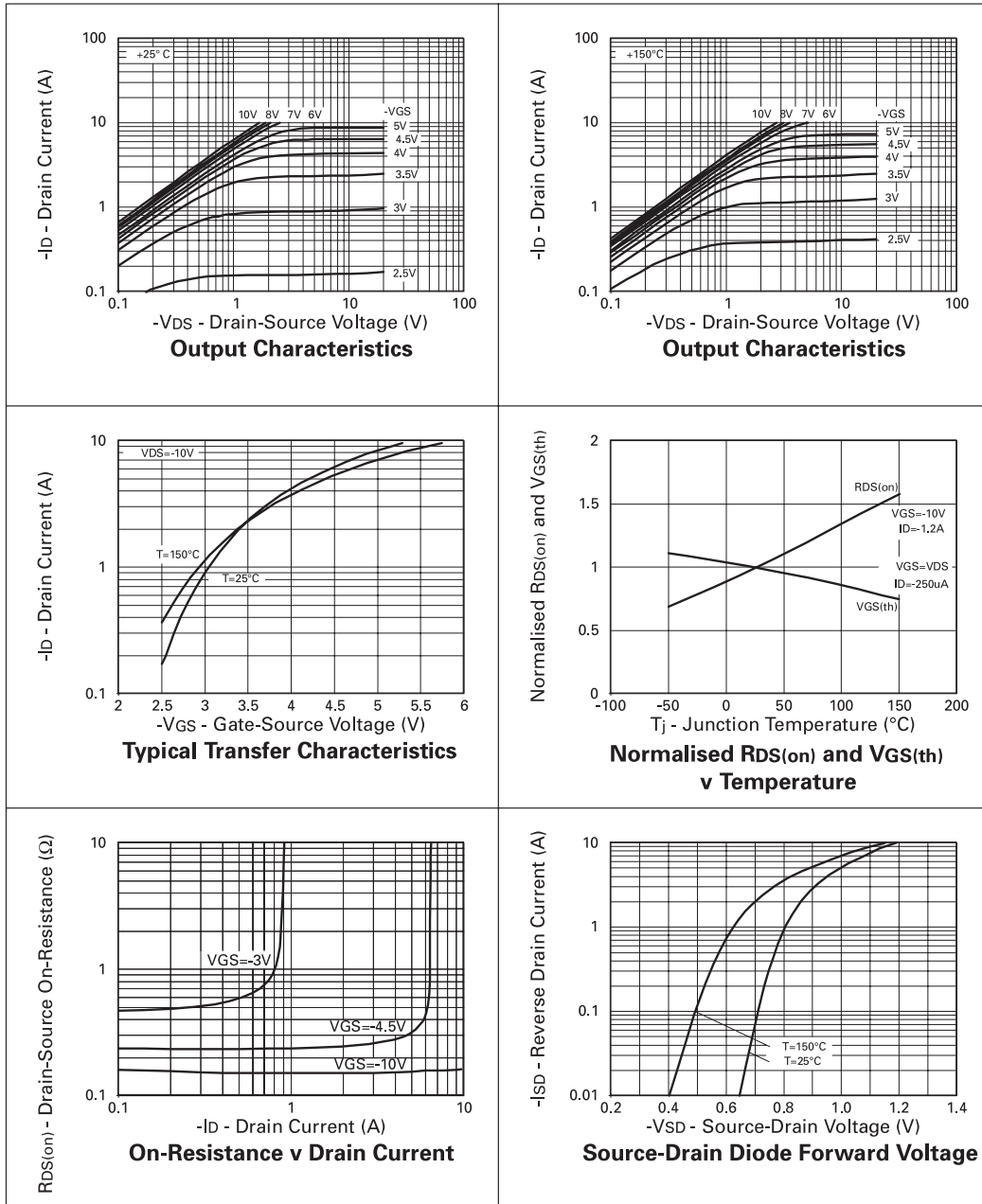
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D=-250\mu A$, $V_{GS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}			-1	μA	$V_{DS}=-30V$, $V_{GS}=0V$
Gate-Body Leakage	I_{GSS}			± 100	nA	$V_{GS}=\pm 20V$, $V_{DS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D=-250\mu A$, $V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.185 0.27	Ω Ω	$V_{GS}=-10V$, $I_D=-1.2A$ $V_{GS}=-4.5V$, $I_D=-0.6A$
Forward Transconductance (3)	g_{fs}	0.92			S	$V_{DS}=-10V$, $I_D=-0.6A$
DYNAMIC (3)						
Input Capacitance	C_{iss}		270		pF	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1MHz$
Output Capacitance	C_{oss}		80		pF	
Reverse Transfer Capacitance	C_{rss}		30		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		2.6		ns	$V_{DD}=-15V$, $I_D=-1.2A$ $R_G=6.2\Omega$, $R_D=6.2\Omega$ (Refer to test circuit)
Rise Time	t_r		4.8		ns	
Turn-Off Delay Time	$t_{d(off)}$		13.1		ns	
Fall Time	t_f		9.3		ns	
Total Gate Charge	Q_g			7	nC	$V_{DS}=-24V$, $V_{GS}=-10V$, $I_D=-1.2A$ (Refer to test circuit)
Gate-Source Charge	Q_{gs}			1.2	nC	
Gate Drain Charge	Q_{gd}			2	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			-0.95	V	$T_J=25^{\circ}C$, $I_S=-1.2A$, $V_{GS}=0V$
Reverse Recovery Time (3)	t_{rr}		21.4		ns	$T_J=25^{\circ}C$, $I_F=-1.2A$, $di/dt=100A/\mu s$
Reverse Recovery Charge(3)	Q_{rr}		15.7		nC	

NOTES:

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

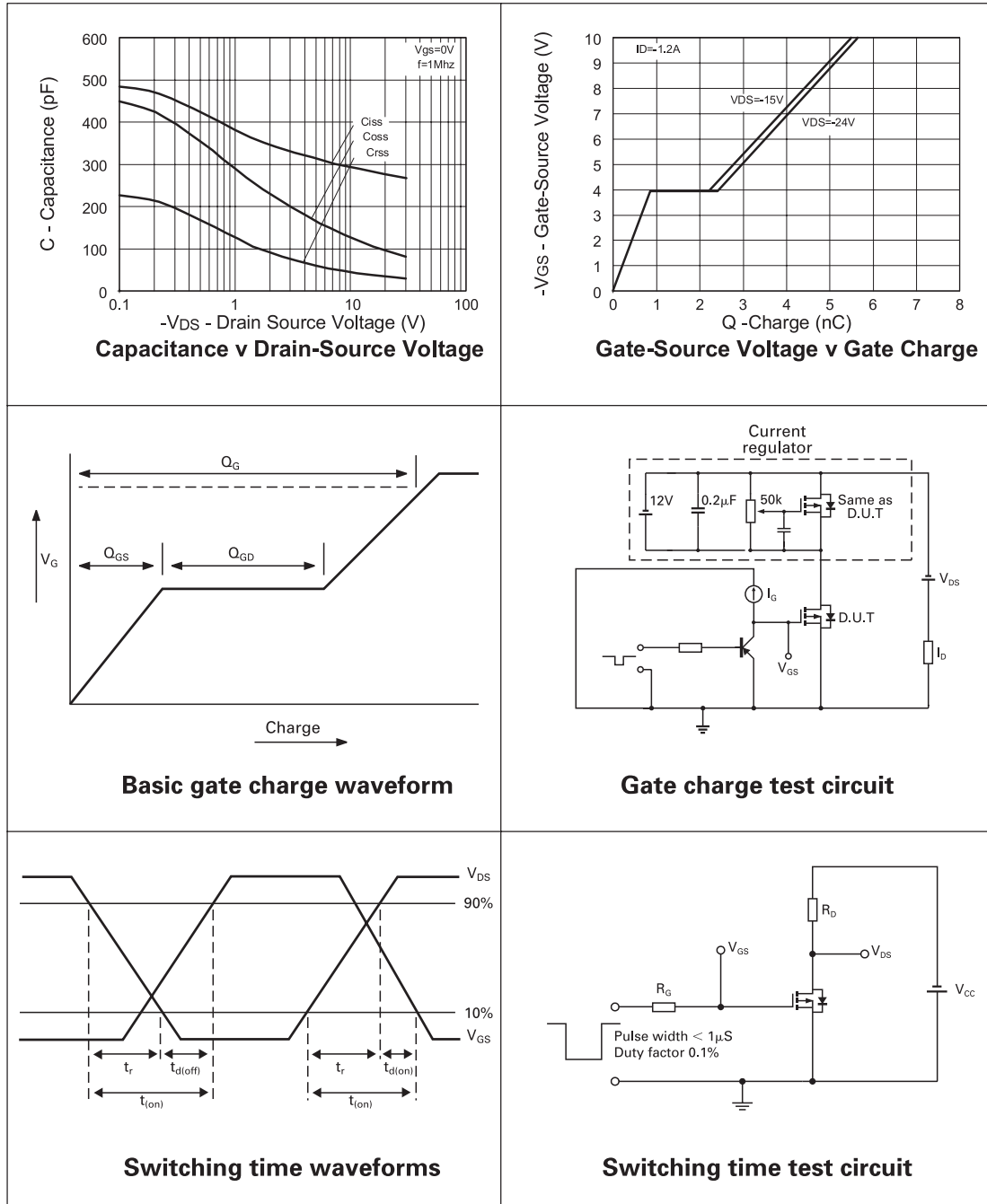
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P-CHANNEL CHARACTERISTICS



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P-CHANNEL TYPICAL CHARACTERISTICS

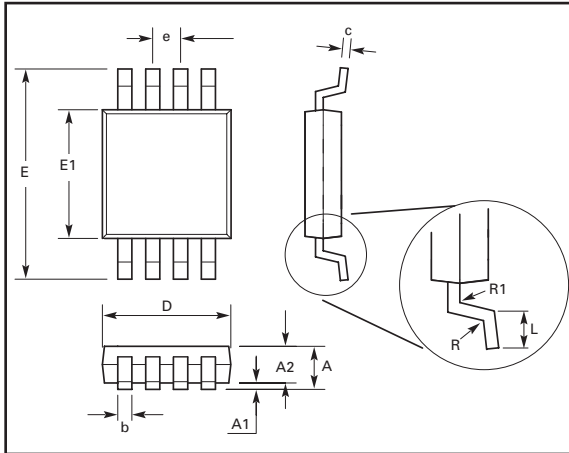


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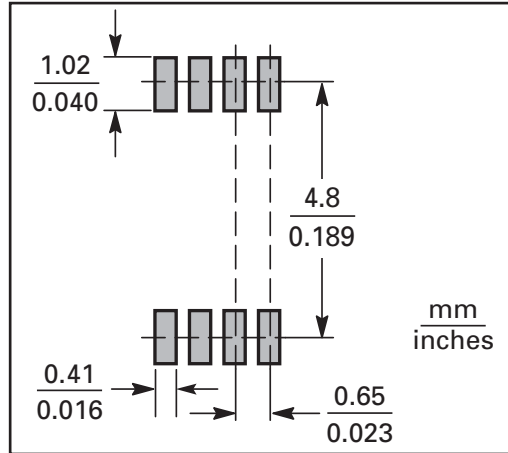
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PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.91	1.11	0.036	0.044
A1	0.10	0.20	0.004	0.008
B	0.25	0.36	0.010	0.014
C	0.13	0.18	0.005	0.007
D	2.95	3.05	0.116	0.120
e	0.65NOM		0.0256	
e1	0.33NOM		0.0128	
E	2.95	3.05	0.116	0.120
H	4.78	5.03	0.188	0.198
L	0.41	0.66	0.016	0.026
θ°	0°	6°	0°	6°

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